Supplemental Materials

Movable triple points and Dirac points in centrosymmetric AB$_2$ (A=Cr, Mo; B=Si, Ge) compounds

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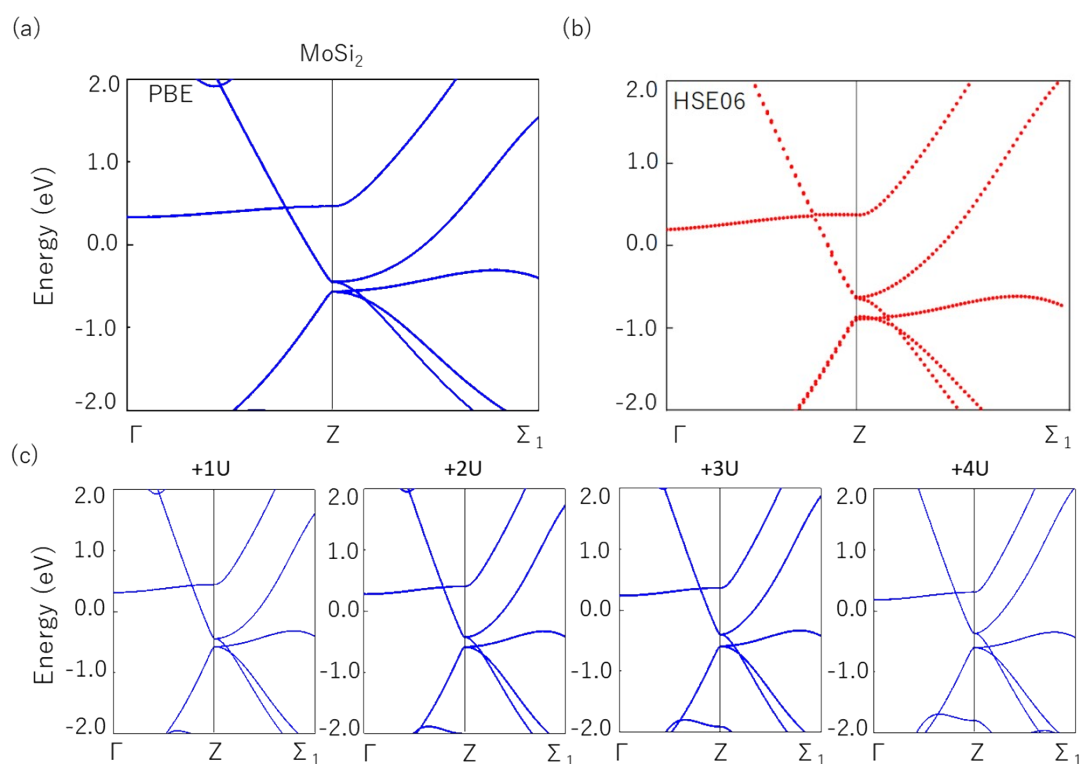E-mail: xuefangdai@126.com; gdliu1978@126.com

Figure S1. Electric band structure of MoSi$_2$ without SOC calculated by PBE (a), HSE (b) and PBE+U (c).